Electronic Supplementary Information

Enhanced Performance in Polymer Light Emitting Diodes using Indium-Zinc-Tin Oxide Transparent Anode by Controlling of Oxygen Partial Pressure at Room Temperature

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Table S1. Chemical composition of the IZTO films deposited at various oxygen partial pressures.

Oxygen partial pressure (%)	In	Zn	Sn	O
0.0	15.52(66.7)	4.66(20.0)	3.10(13.0)	76.72
1.0	15.45(66.5)	4.65(20.0)	3.15(13.6)	76.75
2.0	15.39(66.2)	4.63(19.9)	3.21(13.8)	76.78
3.0	15.30(68.3)	3.41(15.2)	3.70(16.5)	77.60
4.0	13.98(64.9)	3.83(17.8)	3.74(17.3)	78.45

The composition of the IZTO films was estimated using a field emission SEM/EDS(S-4800, HITACHI/7593-H, HORIBA) as shown in Table S1. Chemical composition of the IZTO films deposited at various oxygen partial pressures shows that the zinc (tin) contents (Zn(Sn)/In+Zn+Sn)) are nearly 20.0-15.2 (13-17.3) at.% and slightly decreases with the increase with increase to 3% oxygen partial pressure content. Especially, the composition of IZTO film at 3% oxygen partial pressure shows closely approaching target composition.